

REMARKS

Reconsideration and allowance of the above referenced application are respectfully requested.


After entry of this amendment, the elected and new claims should be considered by the Examiner.

In view of the above amendments, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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VERSION TO SHOW CHANGES MADE

In the Claims:

Claims 1, 7, 8, 9, 10, 11, 18, 19, 21, and 31 have been amended as follows.

1. (Amended) A method of manufacturing a semiconductor device, wherein, a material having a tensile stress of  $8 \times 10^9$  dynes/cm<sup>2</sup> or more is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

7. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a temperature range of between 500 and 900°C is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

8. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a pressure range of between 0.1 and 3 Torr is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

9. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD with a gas containing chlorine as a material gas is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

10. (Amended) A method of manufacturing a semiconductor device, wherein a silicon nitride film having an N/Si composition ratio of between 1.2 and 1.4 is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said silicon nitride film.

11. (Amended) A method of manufacturing a semiconductor device, wherein a silicon nitride film formed by LPCVD is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said silicon nitride film.

18. (Amended) A method of manufacturing a semiconductor device according to any one of claims 1 and 7 to 11, wherein said semiconductor film is a non-single crystal semiconductor film.

19. (Amended) A method of manufacturing a semiconductor device according to any one of claims 1 and 7 to 11, wherein said semiconductor film is a crystalline silicon film.

21. (Amended) A method of manufacturing a semiconductor device, wherein after a material is formed in contact with a semiconductor film that is formed on a substrate, heat treatment is performed to thereby set a tensile stress of said material to  $8 \times 10^9$  dynes/cm<sup>2</sup> or more and at the same time an impurity element in said semiconductor film is gettered into said material.

31. (Amended) A method of manufacturing a semiconductor device, wherein after a material is formed in contact with a semiconductor film that is formed on a substrate, heat treatment is performed to thereby set a composition ratio of N/Si of said material to between 1.2 and 1.4 and at the same time an impurity element in said semiconductor film is gettered into said material.

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New claims ~~44-59~~ have been added.